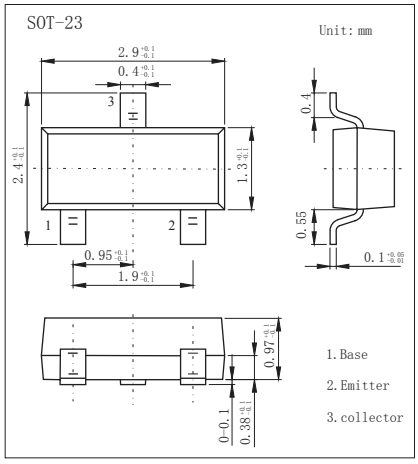
PNP Transistors

KTA1298



■ Features

- Collector Power Dissipation: P_C=200mW
- Collector Current: I_C=-800mA

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	-35	V
Collector-Base Voltage	V_{CBO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-1mA,I_E=0	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA,I_B=0	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-1mA,I_C=0	-5			V
Collector Cut-off Current	I_{CBO}	V_{CB}=-30V, I_E=0			-0.1	uA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	uA
DC Current Gain	h_{FE}	V_{CE}=-1V, I_C=-100mA	100		320	
		V_{CE}=-1V, I_C=-800mA	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-20mA			-0.4	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-10mA		120		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		13		pF

■ h_{FE} Classification

Type	KTA1298-O	KTA1298-Y
Range	100-200	160-320
Marking	KIO	KIY

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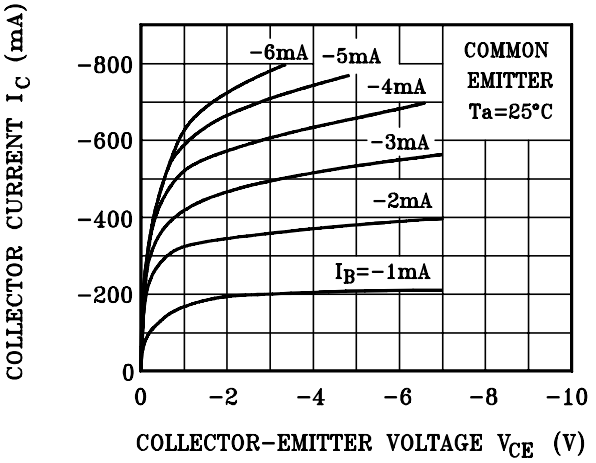
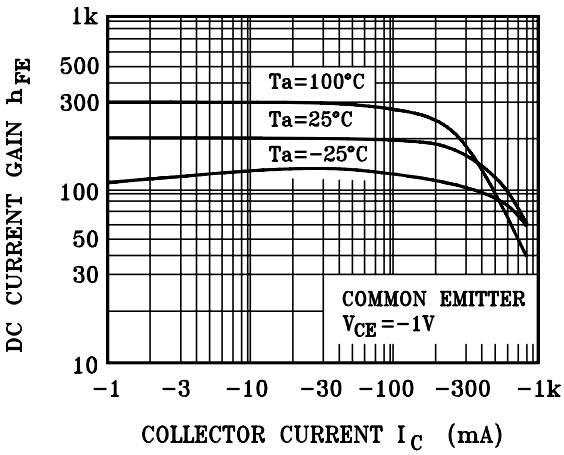
■ Typical Characterisitics

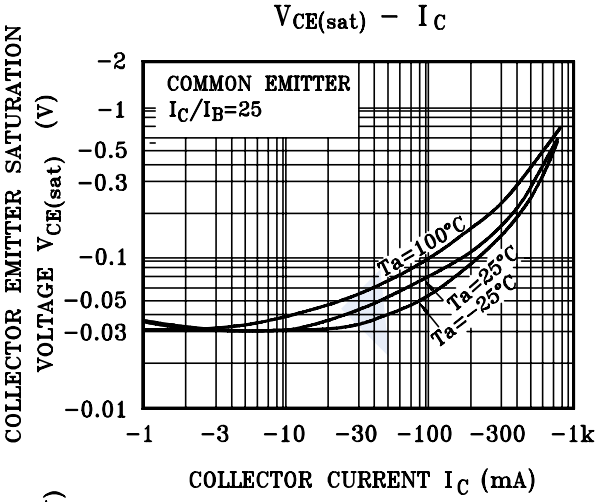
I_C – V_{CE}



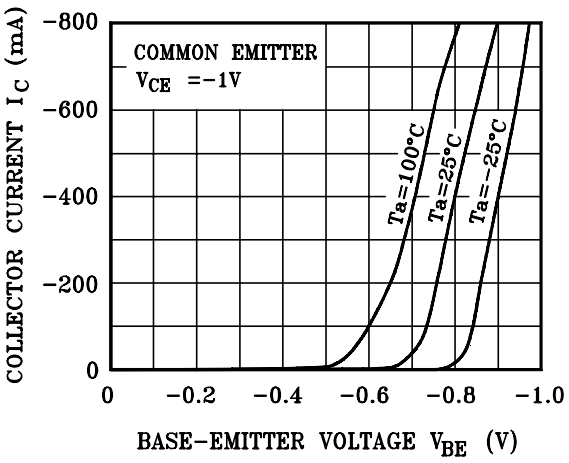
h_{FE} – I_C



$V_{CE(sat)}$ – I_C



I_C – V_{BE}



P_C – T_a